TOSHIBA Transistor Silicon-Germanium NPN Epitaxial Planer Type

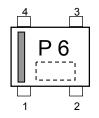
MT4S100T

UHF Low Noise Amplifier Application

FEATURES

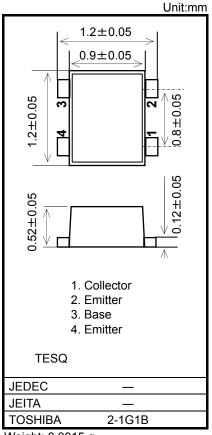
- Low Noise Figure :NF=0.72dB (@f=2GHz)
- High Gain: |S21e|²=17.0dB (@f=2GHz)

Marking



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V _{CBO}	6	V
Collector-Emitter voltage	V _{CEO}	3	V
Emitter-Base voltage	V _{EBO}	1.2	V
Collector-Current	Ι _C	15	mA
Base-Current	Ι _Β	7	mA
Collector Power dissipation	P _C	45	mW
Junction temperature	Tj	150	°C
Storage temperature Range	T _{stg}	-55~150	°C



Weight: 0.0015 g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	f _T	V _{CE} =2V, I _C =10mA, f=2GHz	19	23	_	GHz
Insertion Gain	S21e ²	V _{CE} =2V, I _C =10mA, f=2GHz	14	17.0	_	dB
Noise Figure	NF	V _{CE} =2V, I _C =5mA, f=2GHz		0.72	1.0	dB

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =6V, I _E =0	_	_	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =1V, I _C =0	_	_	1	μA
DC Current Gain	hFE	V _{CE} =2V, I _C =10mA	200	_	400	-
Output Capacitance	C _{ob}	V _{CB} =2V, I _E =0, f=1MHz	_	0.41	0.6	pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =2V, I _E =0, f=1MHz (Note 1)		0.14	0.2	pF

Note 1: Cre is measured by 3 terminal method with capacitance bridge.

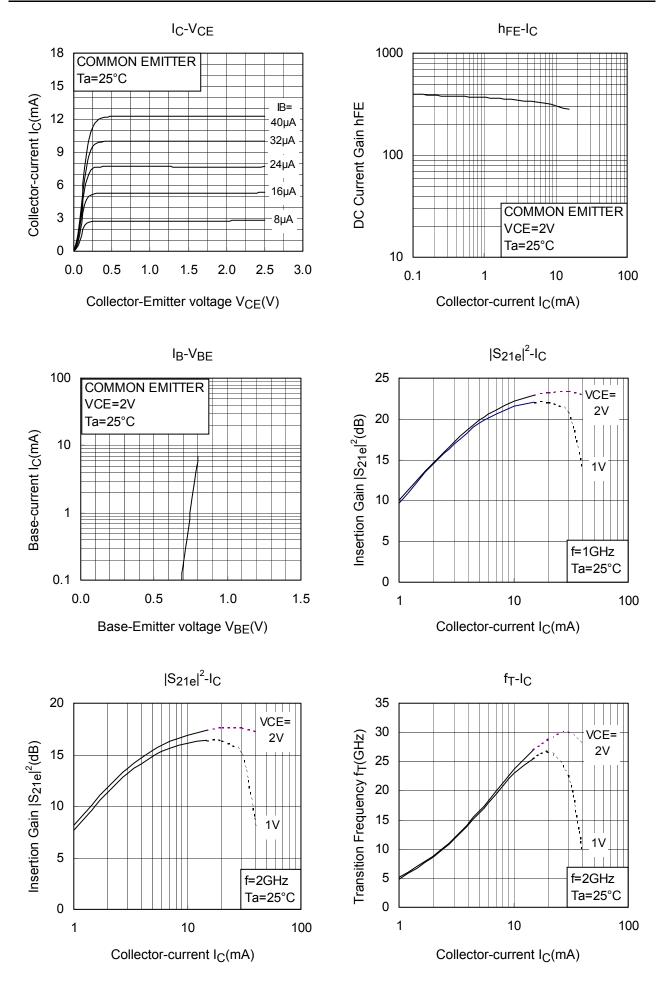
Caution:

This device is sensitive to electrostatic discharge due to applied the high frequency transistor

process of fT=60GHz class is used for this product.

Please make enough tool and equipment earthed when you handle.

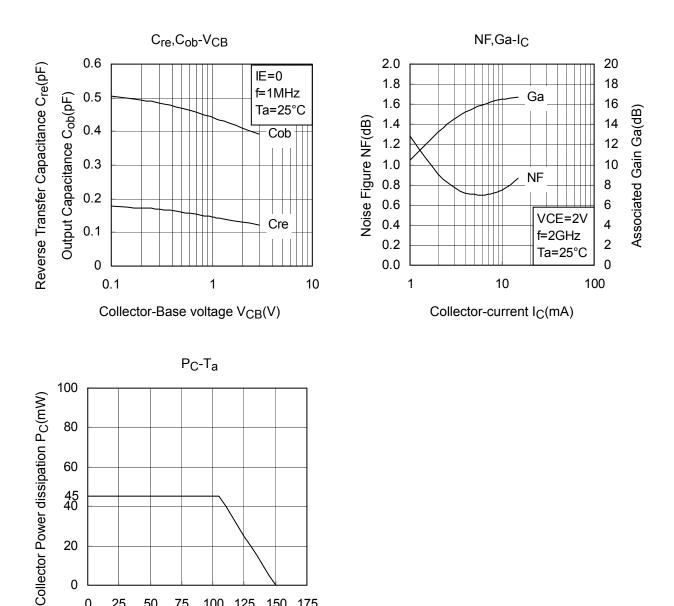
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Ambient temperature Ta(°C)

100 125 150 175



RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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